AMENDMENTS TO THE SPECIFICATION

In the Specification:

Please amend the paragraph at page 1, lines 5-8 as follows:

The present invention generally relates to semiconductor processing and, more particularly, to a system and method for extending resolution of and production of small features [[in]] achievable in nanoprint lithography.

Please amend the paragraph at page 1, line 20 through page 2, line 3 as follows:

The requirement of small features with close spacing between adjacent features requires high resolution lithographic processes. In general, lithography refers to processes for pattern transfer between various media. It is a technique used for integrated circuit fabrication in which a silicon structure is coated uniformly with a radiation-sensitive film ([[the]] a resist or a lithographic coating) and an exposing source (such as optical light, x-rays, or an electron beam) illuminates selected areas of the ~~surface~~ coated silicon structure through an intervening master template. The intervening master template is generally known as a mask, photomask, or reticle for a particular pattern. The lithographic coating is generally a radiation-sensitive coating suitable for receiving a projected image of the subject pattern. Once the image is projected, it is indelibly formed in the coating. The projected image may be either a negative image or a positive image of the subject pattern. Exposure of the coating through a reticle, mask or photomask causes the image area to become either more or less soluble (depending on the coating) in a particular solvent developer. The more soluble areas are removed in the developing process to leave the pattern image in the coating as less soluble polymer.

Please amend the paragraph at page 9, lines 19-30 as follows:

However, the situation is different for light rays 808, 812, 818 and 822. Each of these light rays enters the translucent substrate 800 at its upper surface 830. However, instead of passing through the mask uninterrupted, each of these light rays is absorbed by light absorbing material 860 which has been deposited on the sidewalls of features on the mask. For example, light ray 808 enters mask 800 through the upper surface 830 of the mask. The light passes through the upper portion of the mask until it is absorbed by light absorbing material 860 which has been deposited onto sidewall 862. The situation for light rays 812, 818 and 822 are all similar in that each light ray encounters light absorbing material 860 deposited onto the sidewall of a three-dimensional feature. As a result, the portions of resist ~~882~~ <u>852</u> located directly below the light absorbing material deposited onto the sidewalls of the three dimensional features are not exposed by light. In Fig. 8, the unexposed areas are 870, 872, 874 and 876.

Please delete the original Abstract and substitute the following as shown on the subsequent page: